

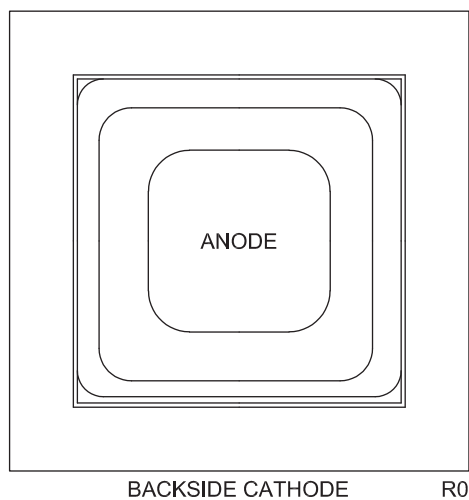
PROCESS CPZ34R
Transient Voltage Suppressor
6.2 Volt TVS Chip



PROCESS DETAILS

Die Size	6.7 x 6.7 MILS
Die Thickness	3.54 MILS
Anode Bonding Pad Area	4.5 x 4.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au.As - 12,000Å

GEOMETRY



GROSS DIE PER 5 INCH WAFER

374,272

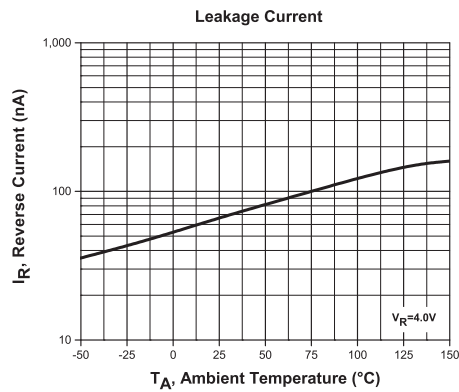
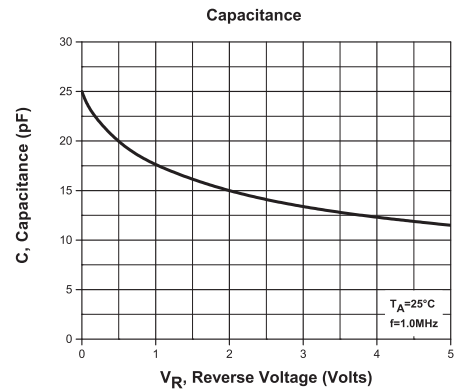
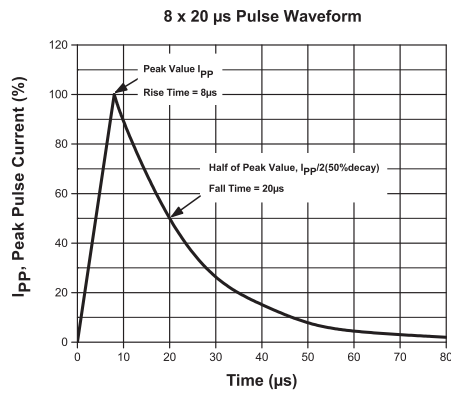
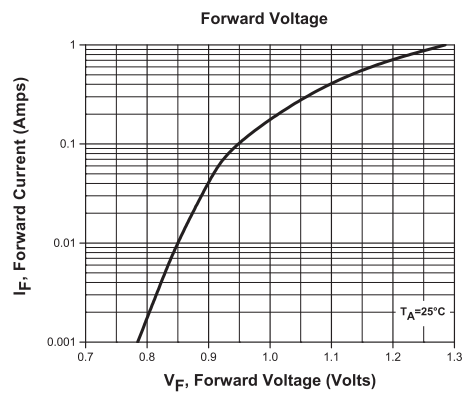
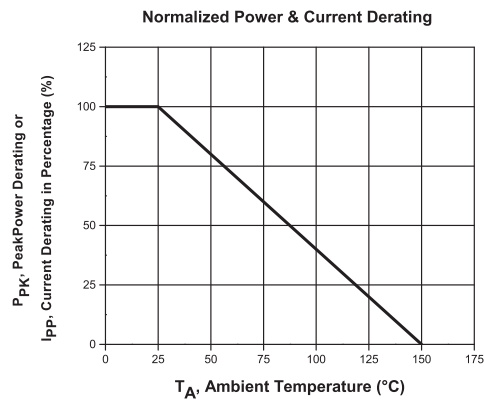
PRINCIPAL DEVICE TYPE

CTLTVS6V2

R0 (17-January 2013)

PROCESS CPZ34R

Typical Electrical Characteristics



R0 (17-January 2013)